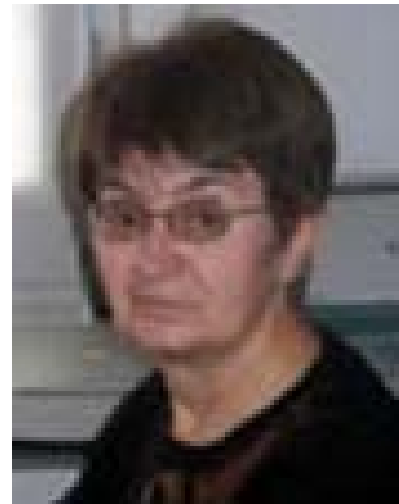


**Name: Kaschieva Sonia**  
(family) (given name)

**Born:** Bulgaria.

**Graduate** from Sofia State University  
“Sv.Kl.Ohridsky”, 1966, Physics  
(Scientific profile) with a specialization in  
Atomic Physics;



**PhD degree in Physics** was conferred in 1978, G. Nadjakov Institute of Solid State Physics (ISSP) Sofia Bulgaria

**PhD Thesis:** " Investigation of the radiation defects in MOS structures."

**Doctor of Physical and Mathematical Sciences ( DSc) degree** (conferred in 1999)  
in **Joint Institute of Nuclear Research (JINR) Dubna, Russia;**

**DSc Thesis:** "Generation and annealing of the radiation defects in MOS structures."

**Associate Professor:** since 1995 till 2004 (ISSP-BAS).

**Professor:** since 2004 and currently (ISSP- Bulgarian Academy of Sciences).

### **Visiting research positions**

1973 Visiting scholar, El.Eng.Dept., Lehigh University of Bethlehem, USA

1976-77 Visiting scholar Inst.Semicond.Phys, Kiev, Ukraina

1996- **up to now** Visiting prof., JINR, Russia

2000 Visiting prof., Rossendorf, Germany

**Fields of expertise:** Semiconductor hetero-structures, Interfaces, Radiation defects, Interaction of gamma, high-energy electrons, neutrons, Re, UV with Si-SiO<sub>2</sub> structures, Ion implantation

### **Main research results:**

- Investigation on the radiation defects in MOS structures in a result of gamma, neutrons, electrons irradiation, ion implantation.
- Interaction of radiation defects in ion implanted MOS structures with gamma, neutrons, electrons UV and Re irradiation.
- UV annealing of the radiation defects in MOS systems
- Effects of high energy (MeV) electron irradiation on the properties of the Si-SiO<sub>2</sub> and MOS structures.

### **International collaboration:**

- Joint Institute of Nuclear Research, Dubna, Russia (7 Joint Projects with Laboratory of Nuclear Reactions ( LNR)

- Ural Branch of Russian Academy of Sciences, Institute of Metal Physics (Ekaterinburg, Russia)

### Some publications

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